

247252US2SDIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

KEIJI HOSOTANI :

SERIAL NO: NEW DIV APPLICATION :

FILED: HEREWITH :

FOR: SEMICONDUCTOR MEMORY DEVICE UTILIZING TUNNEL MAGNETO
RESISTIVE EFFECTS AND METHOD FOR MANUFACTURING THE SAME

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VA 22313

SIR:

Prior to examination on the merits, please amend the above-identified divisional application as follows:

Amendment to the Specification begins on page 2.

Amendments to the Claims begin on page 3 of this paper.

Remarks/Arguments begin on page 7 of this paper.